

FORM 1449* INFORMATION DISCLOSURE STATEMENT IN AN APPLICATION (Use several sheets if necessary)	Docket Number: 10873.1333USW1	Application Number: 10/719,412
	Applicant: SUGITA et al.	
	Filing Date: November 21, 2003	Group Art Unit: Unknown

[illegible]

<div style="border: 1px solid black; padding: 5px; display: inline-block;"> 23552 <small>PATENT TRADEMARK OFFICE</small> </div>	
EXAMINER <i>R. Lee T. Smith</i>	DATE CONSIDERED <i>6/29/09</i>
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form for next communication to the Applicant.	

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U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	6,312,840	11.2001	Kumagai et al.			
	2001/0053053	12.2001	Saito et al.			
	6,169,303	01.2001	Anthony			
	2002/0047145	04.2002	Nickel			
	2002/0039264	04.2002	Ohsawa et al.			

FOREIGN PATENT DOCUMENTS

	DOCUMENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
	2000-068569	03.2000	Japan			Abstract	
	2001-236613	08.2001	Japan			Abstract	
	2000-188435	07.2000	Japan			Abstract	
	2002-171012	06.2002	Japan			Abstract	

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

		Koichiro INOMATA, "MRAM Technology Progress and Prospect" Materials Integration Vol. 13, No. 12, P13-18, 2000 (Japanese only)
		T.Miyazaki et al., "Giant Magnetic Tunneling Effect in Fe/Al ₂ O ₃ /Fe Junction", Journal of Magnetism and Magnetic Materials, 139 (1995) L231-L234
		Ping Shang et al., "High-resolution electron microscopy study of tunneling junctions with AlN and Alon barriers", Journal of Applied Physics, Vol. 89, No. 11, pp. 6874-6876, 1 June 2001
		Yasunari SUGITA et al., "Tunneling Magnetoresistance Enhancement for Pt-Added Magnetic Tunnel Junctions", Japanese Journal of Applied Physics, Vol. 41, No. 10A, pp. L1072-1074, October 1, 2002
		Nozomu MATSUKAWA et al., "Thermally stable exchange-biased magnetic tunnel junctions over 400° C" Applied Physics Letter, Vol. 81, No. 25, pp. 4784-4786, December 16, 2002

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EXAMINER

DATE CONSIDERED

6/29/04

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